

UNISONIC TECHNOLOGIES CO., LTD

2N7002ZT **Preliminary Power MOSFET**

300m Amps, 60 Volts DUAL **N-CHANNEL ENHANCEMENT MODE MOSFET**

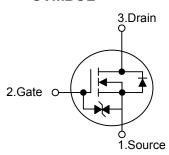
DESCRIPTION

The UTC 2N7002ZT uses advanced technology to provide excellent R_{DS(ON)}, low gate charge and low gate voltages during operation. This device is suitable for use as a load switch or in PWM applications.

FEATURES

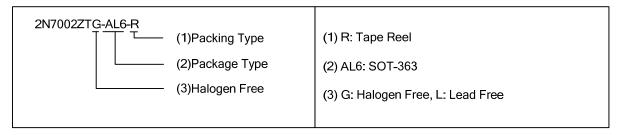
- * Low Reverse Transfer Capacitance (C_{RSS} = typical 3.0 pF)
- * ESD Protected
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness



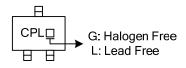


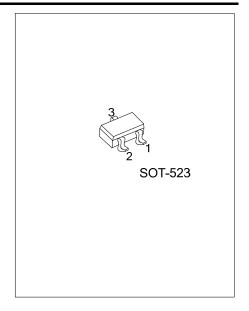
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2N7002ZTL-AN3-R	2N7002ZTG-AN3-R	SOT-523	S	G	D	Tape Reel	



MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Drain Current	Continuous	ı	300	mA	
	Pulse(Note 2)	I _D	800		
Power Dissipation		P_{D}	200	mW	
Derating above T _A =25°C		FD	1.6	mW/°C	
Junction Temperature		T_J	+150	°C	
Storage Temperature		T _{STG}	-55 ~ + 150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

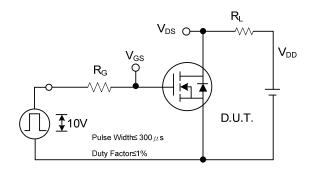
■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =10 μ A	60			V		
Drain-Source Leakage Current	I_{DSS}	V _{DS} =60V, V _{GS} =0V			1.0	μΑ		
Gate-Source Leakage Current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±10	μA		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	V _{DS} =10V, I _D =1mA	1.0	1.85	2.5	V		
Static Drain-Source On-Resistance (Note)		V _{GS} =10V, I _D =0.5A, T _J =125°C			13.5	Ω		
Static Dialii-Source Off-Resistance (Note)		V _{GS} =5V, I _D =0.05A			7.5			
DYNAMIC PARAMETERS								
Input Capacitance	C _{ISS}			25	50	pF		
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		10	25	pF		
Reverse Transfer Capacitance	C_{RSS}			3.0	5.0	рF		
SWITCHING PARAMETERS								
Turn-ON Delay Time	$t_{D(ON)}$	I _D =0.2 A, V _{DD} =30V, V _{GS} =10V,		12	20	ns		
Turn-OFF Delay Time	$t_{D(OFF)}$	$R_L=150\Omega$, $R_G=10\Omega$		20	30	ns		
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS								
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} =0V, Is=115mA (Note)		0.88	1.5	V		
Maximum Pulsed Drain-Source Diode	Lead				0.8	Α		
Forward Current	I _{SM}				0.0	Α		
Maximum Continuous Drain-Source Diode	ls				115	mA		
orward Current					113	IIIA		

Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

^{2.} Pulse width \leq 300 µs, Duty cycle \leq 1%

■ TEST CIRCUITS AND WAVEFORMS





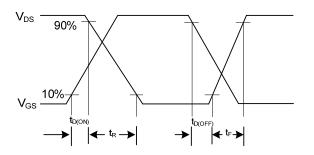


Fig. 2B Switching Waveforms

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